

Silicon PNP Power Transistors

2SB511

DESCRIPTION

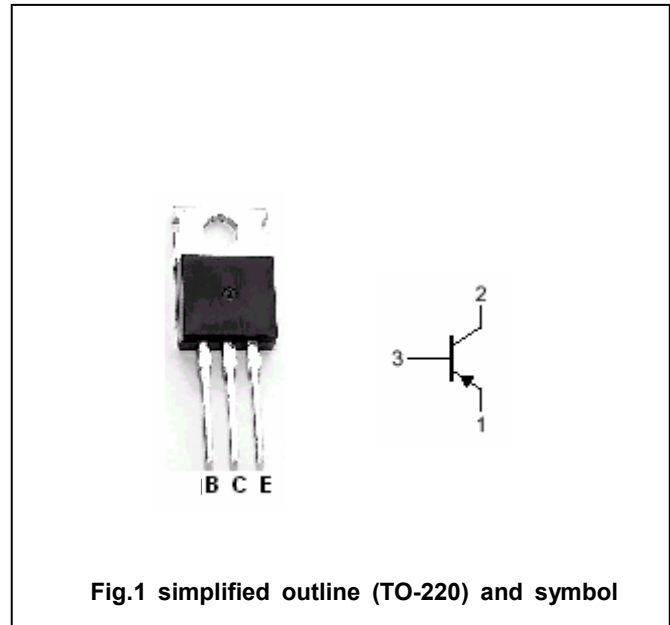
- With TO-220C package
- Complement to type 2SD325
- Low collector saturation voltage

APPLICATIONS

- Designed for use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-35	V
V_{CEO}	Collector-emitter voltage	Open base	-35	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-1.5	A
I_{CM}	Collector current -peak		-3.0	A
P_C	Collector dissipation	$T_a=25^\circ\text{C}$	1.75	W
		$T_C=25^\circ\text{C}$	10	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-50~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-35			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A; I _B =-0.15A			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-1A; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-20V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	I _C =-1A; V _{CE} =-2V	40		320	
h _{FE-2}	DC current gain	I _C =-0.1A; V _{CE} =-2V	35			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-5V		8		MHz

◆ h_{FE-1} Classifications

C	D	E	F
40-80	60-120	100-200	160-320

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)